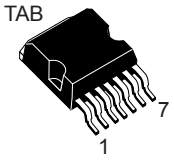
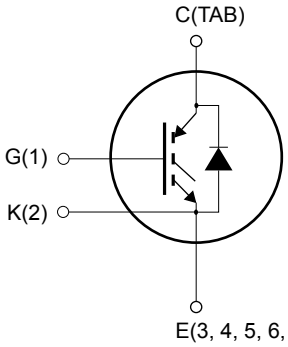
GH50H65DRB2-7AG

Datasheet

Automotive-grade trench gate field-stop 650 V, 50 A high-speed HB2 series IGBT featuring freewheeling diode in an H²PAK-7 package



H²PAK-7



IGBTG1K2E34567CTAB

Features

- AEC-Q101 qualified
- Maximum junction temperature: T_J = 175 °C
- High speed switching series
- Minimized tail current
- Low $V_{CE(sat)}$ = 1.6 V (typ.) @ I_C = 50 A
- Tight parameter distribution
- Low thermal resistance
- Positive $V_{CE(sat)}$ temperature coefficient
- Co-packed with high ruggedness rectifier diode
- Excellent switching performance thanks to the extra driving kelvin pin

Application

- On board charger (OBC)
- PFC converter - single phase input

Description

The newest IGBT 650 HB2 series represents an evolution of the advanced proprietary trench gate field-stop structure. The performance of the HB2 series is optimized in terms of conduction, thanks to a better $V_{CE(sat)}$ behavior at low current values, as well as in terms of reduced switching energy.

Product status link
GH50H65DRB2-7AG

Product summary	
Order code	GH50H65DRB2-7AG
Marking	G50H65RB2A
Package	H²PAK-7
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage (V_{GE} = 0 V)	650	V
I_C	Continuous collector current at T_C = 25 °C	108(1)	A
	Continuous collector current at T_C = 100 °C	68	
I_{CP}(2)	Pulsed collector current (t_p ≤ 1 µs, T_J < 175 °C)	200	A
V_{GE}	Gate-emitter voltage	±20	V
	Transient gate-emitter voltage (t_p ≤ 10 µs)	±30	
I_F	Continuous forward current at T_C = 25 °C	50(1)	A
	Continuous forward current at T_C = 100 °C	30	
I_{FP}(2)	Pulsed forward current	120	A
P_{TOT}	Total power dissipation at T_C = 25 °C	385	W
T_{STG}	Storage temperature range	-55 to 150	°C
T_J	Operating junction temperature range	-55 to 175	°C

1. *Limited by package.*
2. *Defined by R_{thJC} and limited by maximum junction temperature, not tested in production.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case, IGBT	0.39	°C/W
	Thermal resistance, junction-to-case, diode	0.75	
R_{thJA}	Thermal resistance, junction-to-ambient	50	°C/W

2 Electrical characteristics

T_J = 25 °C unless otherwise specified.

Table 3. Static characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	V_{GE} = 0 V, I_C = 1 mA	650			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE} = 15 V, I_C = 50 A		1.6	2.0	V
		V_{GE} = 15 V, I_C = 50 A, T_J = 125 °C		1.8		
		V_{GE} = 15 V, I_C = 50 A, T_J = 175 °C		1.9		
V_F	Forward on-voltage	I_F = 30 A		1.05		V
		I_F = 30 A, T_J = 175 °C		0.93		
$V_{GE(th)}$	Gate threshold voltage	V_{CE} = V_{GE}, I_C = 1 mA	5	6	7	V
I_{CES}	Collector cut-off current	V_{GE} = 0 V, V_{CE} = 650 V			25	µA
I_{GES}	Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = ±20 V			±100	nA

Table 4. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	V_{CE} = 25 V, f = 1 MHz, V_{GE} = 0 V	-	2918	-	pF
C_{oes}	Output capacitance		-	129	-	pF
C_{res}	Reverse transfer capacitance		-	75	-	pF
Q_g	Total gate charge	V_{CC} = 520 V, I_C = 50 A, V_{GE} = 0 to 15 V (see Figure 22. Gate charge test circuit)	-	152	-	nC
Q_{ge}	Gate-emitter charge		-	21	-	nC
Q_{gc}	Gate-collector charge		-	70	-	nC

Table 5. IGBT switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off delay time	V_{CE} = 400 V, I_C = 50 A, V_{GE} = 15 V, R_G = 4.7 Ω (see Figure 21. Test circuit for inductive load switching)	-	117	-	ns
t_f	Current fall time		-	30	-	ns
E_{off} (1)	Turn-off switching energy		-	557	-	µJ
$t_{d(off)}$	Turn-off delay time	V_{CE} = 400 V, I_C = 50 A, V_{GE} = 15 V, R_G = 4.7 Ω, T_J = 175 °C (see Figure 21. Test circuit for inductive load switching)	-	138	-	ns
t_f	Current fall time		-	73	-	ns
E_{off} (1)	Turn-off switching energy		-	964	-	µJ

1. *Including the tail of the collector current.*

Table 6. Diode switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	I_F = 30 A, V_R = 400 V, V_{GE} = 15 V, di/dt = 200 A/µs (1) (see Figure 21. Test circuit for inductive load switching)	-	912	-	ns
Q_{rr}	Reverse recovery charge		-	23	-	nC
I_{rrm}	Reverse recovery current		-	53.6	-	A
dI_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	71	-	A/µs
E_{rr}	Reverse recovery energy		-	2.6	-	µJ
t_{rr}	Reverse recovery time	I_F = 30 A, V_R = 400 V, V_{GE} = 15 V, di/dt = 200 A/µs (1), T_J = 175 °C (see Figure 21. Test circuit for inductive load switching)	-	1016	-	ns
Q_{rr}	Reverse recovery charge		-	69	-	nC
I_{rrm}	Reverse recovery current		-	57	-	A
dI_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	69	-	A/µs
E_{rr}	Reverse recovery energy		-	3.1	-	µJ

1. *Maximum recommended value*

2.1 Electrical characteristics (curves)

Figure 1. Total power dissipation vs temperature

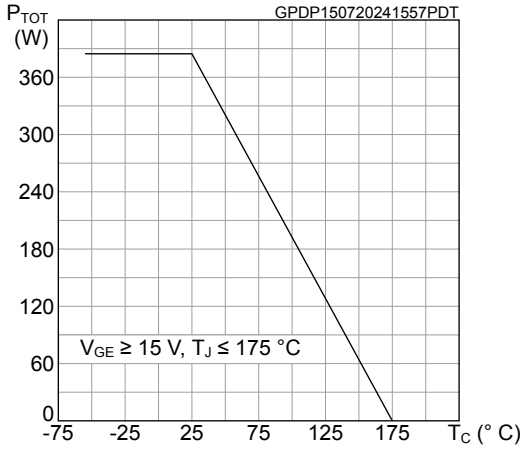


Figure 2. Collector current vs temperature

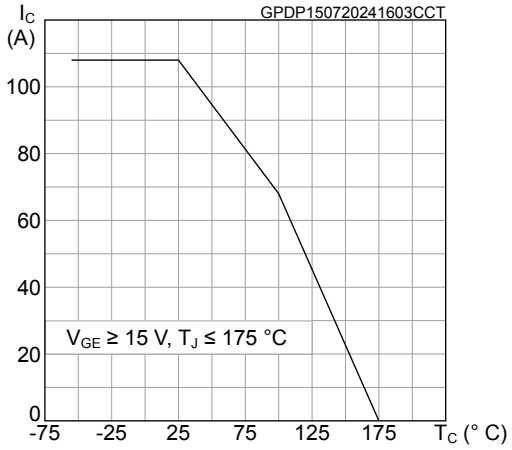


Figure 3. Typical output characteristics (T_J = 25 °C)

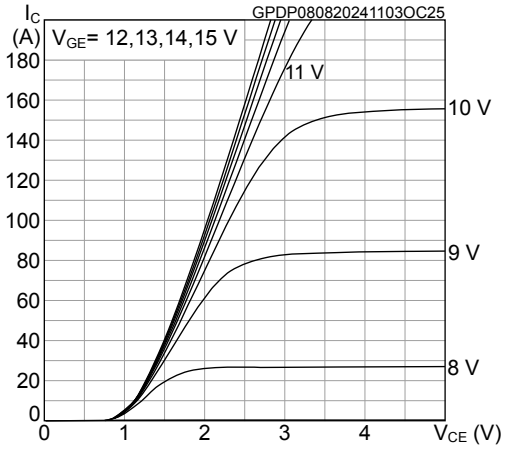


Figure 4. Typical output characteristics (T_J = 175 °C)

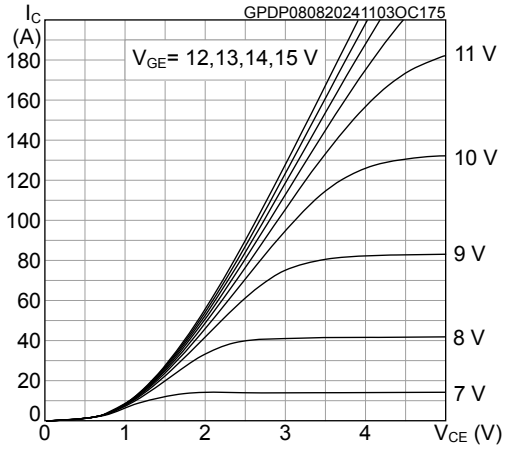


Figure 5. Typical transfer characteristics

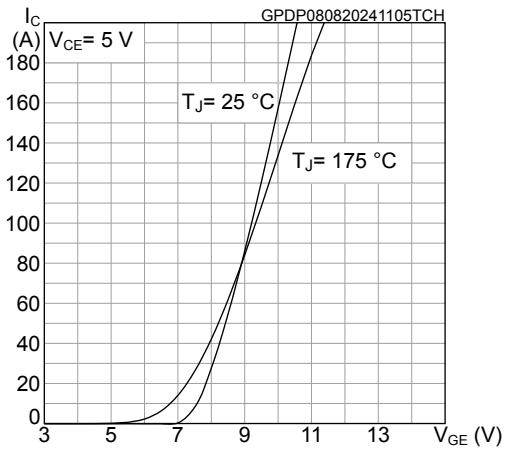


Figure 6. Typical $V_{CE(sat)}$ vs temperature

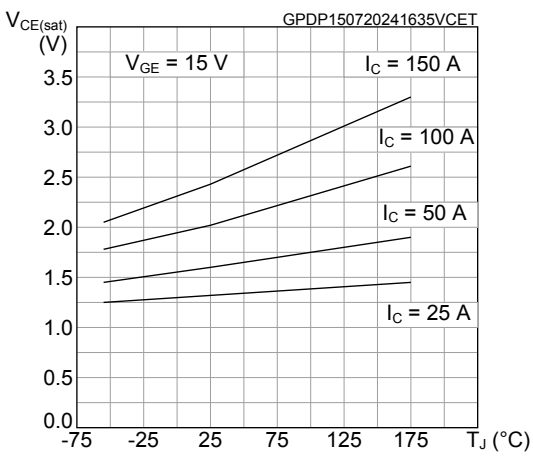


Figure 7. Typical $V_{CE(sat)}$ vs collector current

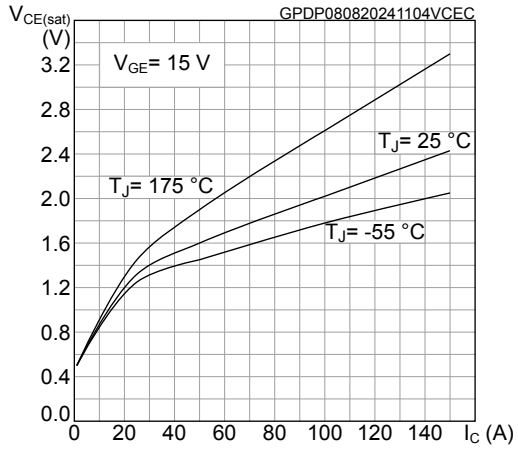


Figure 8. Forward bias safe operating area

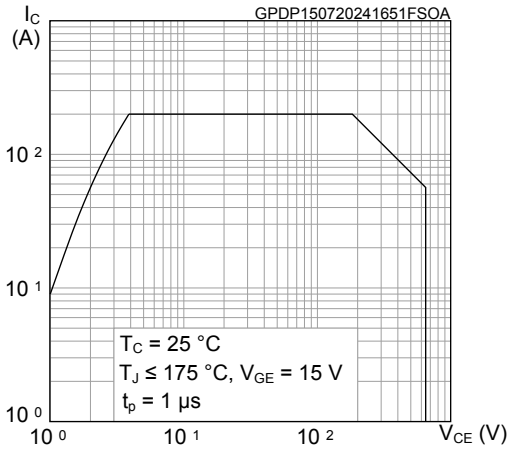


Figure 9. Diode typical forward characteristics

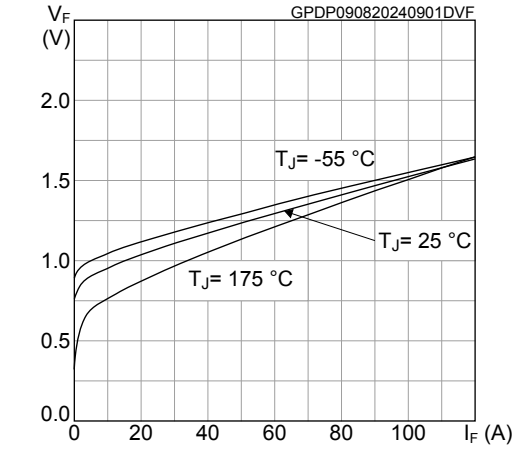


Figure 10. Normalized gate threshold vs temperature

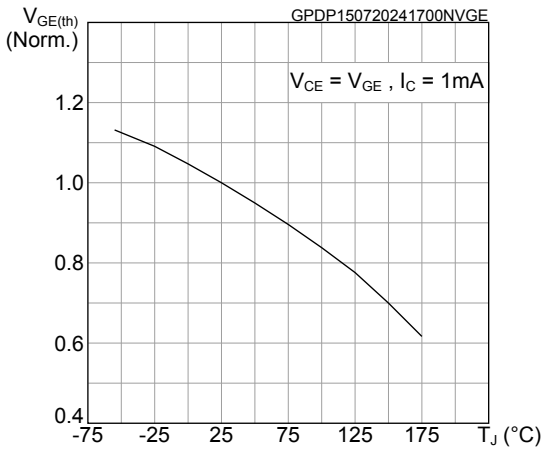


Figure 11. Typical capacitance characteristics

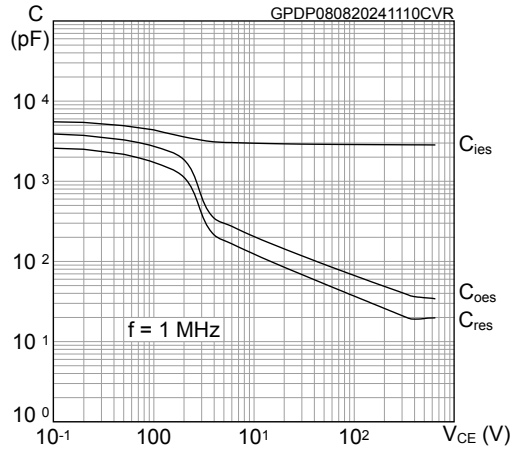


Figure 12. Typical gate charge characteristics

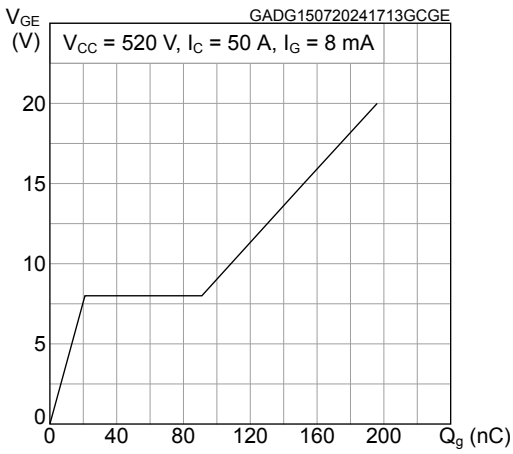


Figure 13. Typical switching energy vs collector current

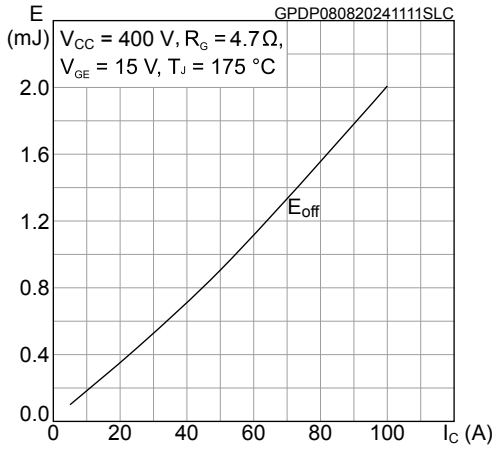


Figure 14. Typical switching energy vs temperature

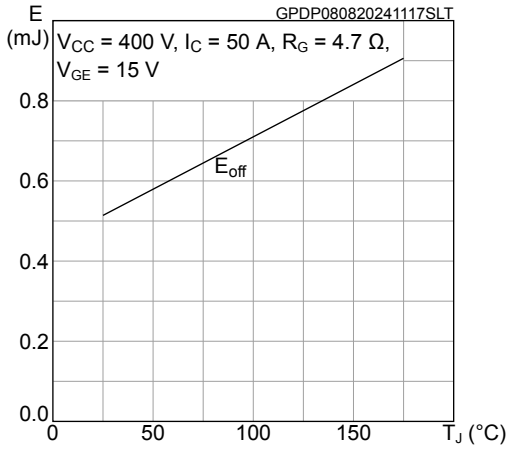


Figure 15. Typical switching energy vs supply voltage

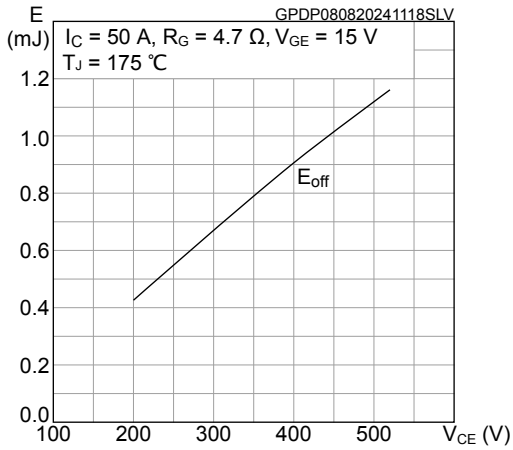


Figure 16. Typical switching energy vs gate resistance

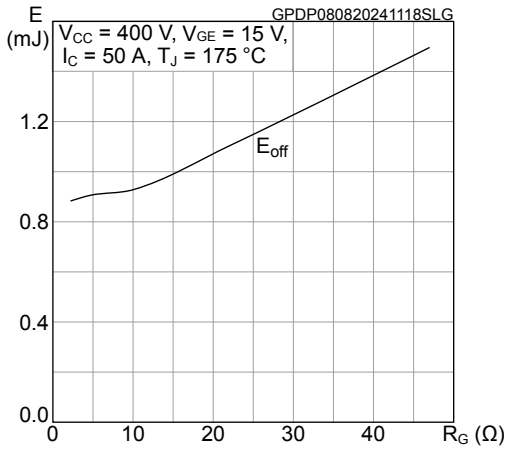


Figure 17. Typical switching times vs collector current

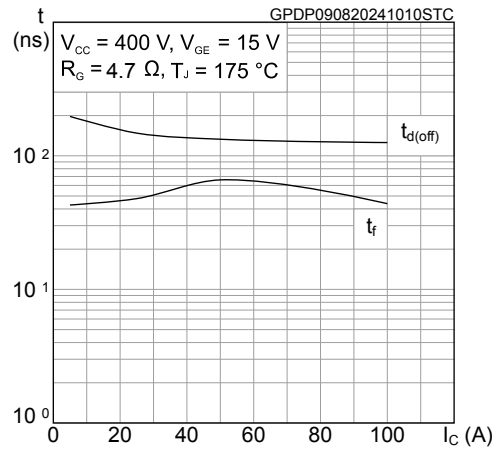


Figure 18. Typical switching times vs gate resistance

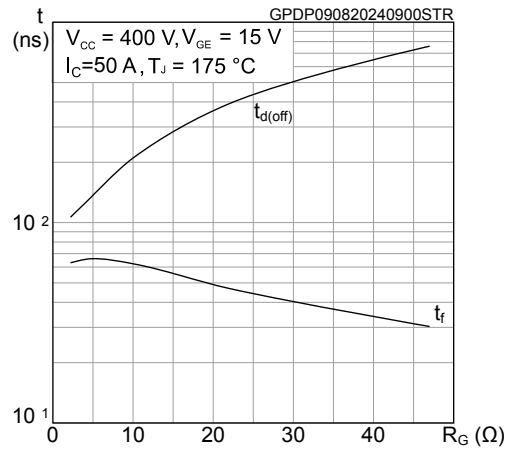


Figure 19. IGBT maximum transient thermal impedance

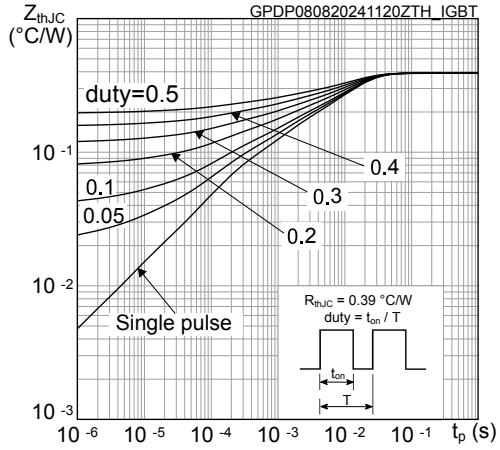
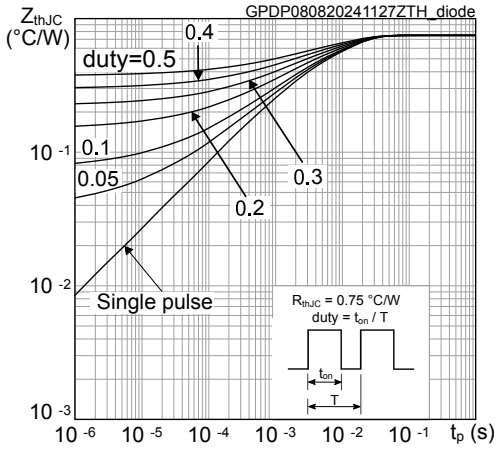


Figure 20. Diode maximum transient thermal impedance



3 Test circuits

Figure 21. Test circuit for inductive load switching

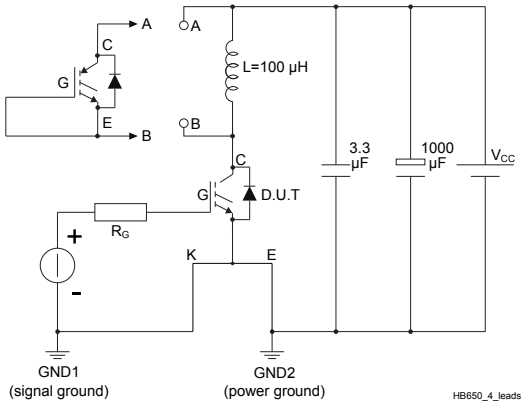


Figure 22. Gate charge test circuit

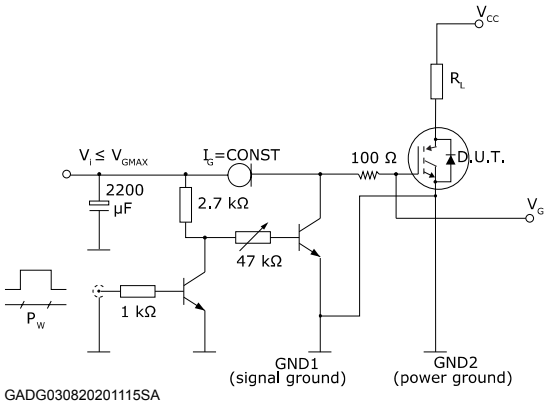


Figure 23. Switching waveform

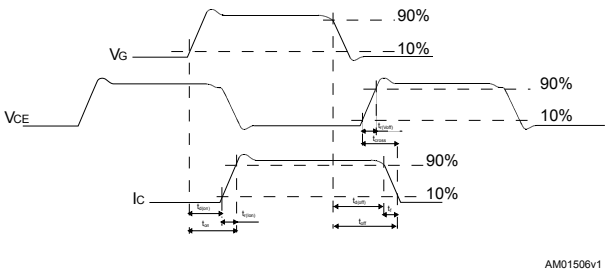
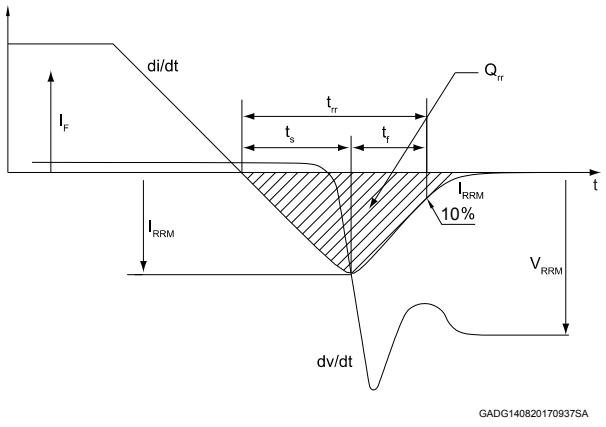


Figure 24. Diode reverse recovery waveform



4 Package information

To meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 H²PAK-7 package information

Figure 25. **H²PAK-7 package outline**

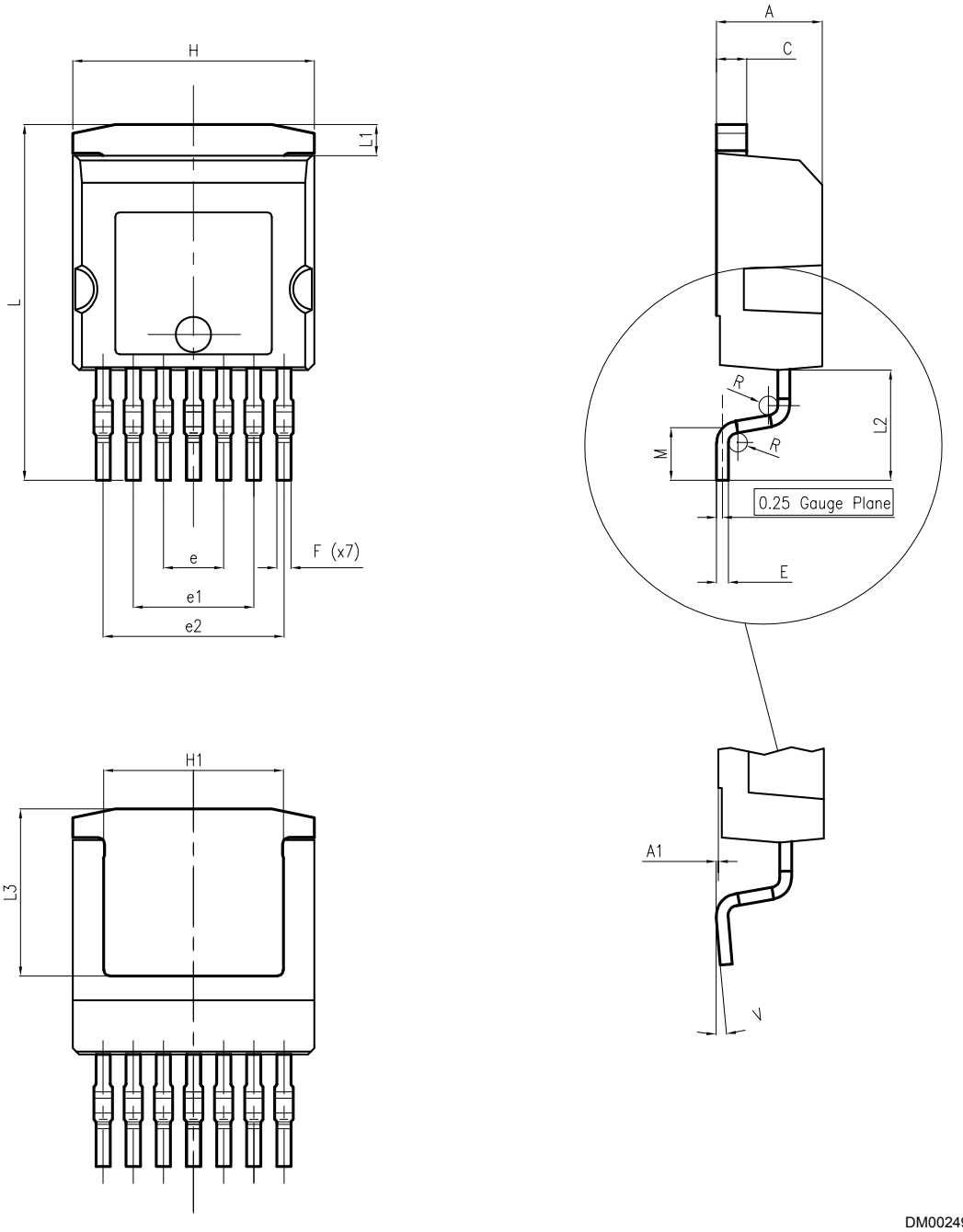
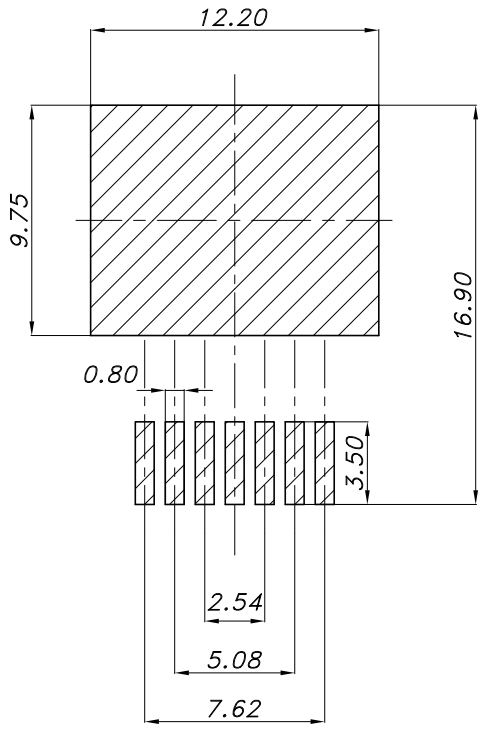


Table 7. **H²PAK-7 package mechanical data**

Dim.	mm	
	Min.	Max.
A	4.30	4.80
A1	0.03	0.20
C	1.17	1.37
e	2.34	2.74
e1	4.88	5.28
e2	7.42	7.82
E	0.45	0.60
F	0.50	0.70
H	10.00	10.40
H1	7.40	8.00
L	14.75	15.25
L1	1.27	1.40
L2	4.35	4.95
L3	6.85	7.25
M	1.90	2.50
R	0.20	0.60
V	0°	8°

Figure 26. **H²PAK-7 recommended footprint**

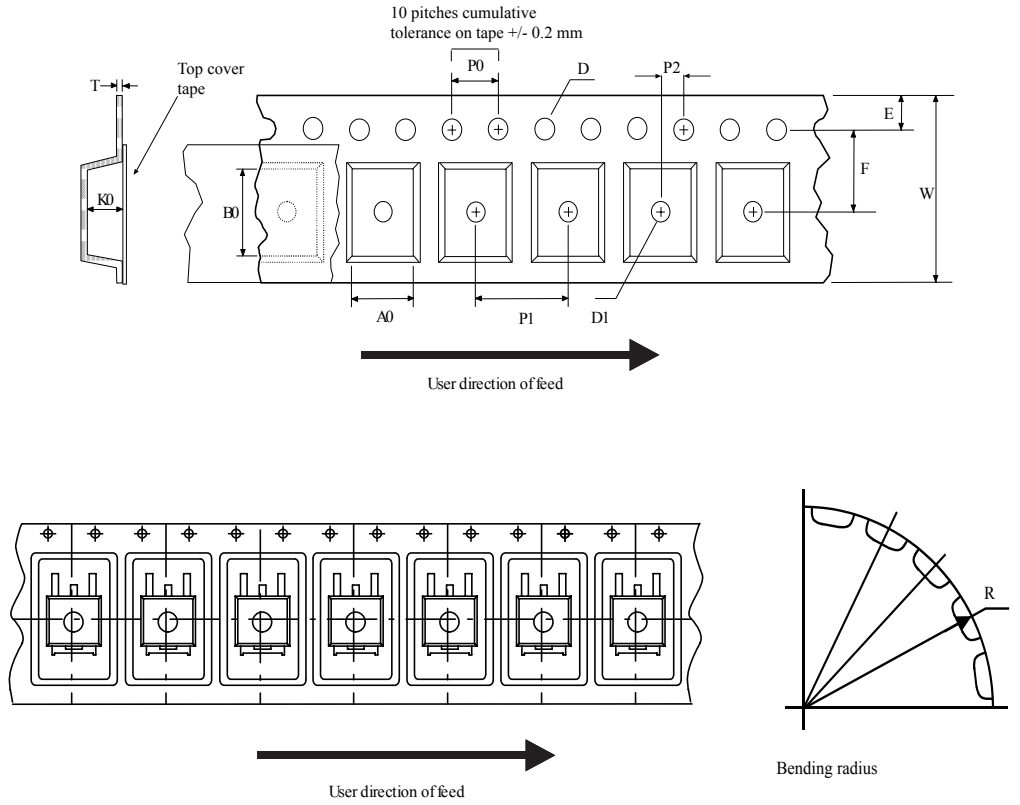


footprint_DM00249216_6

Note: Dimensions are in mm.

4.2 Packing information

Figure 27. **Tape outline**



AM08852v2

Figure 28. **Reel outline**

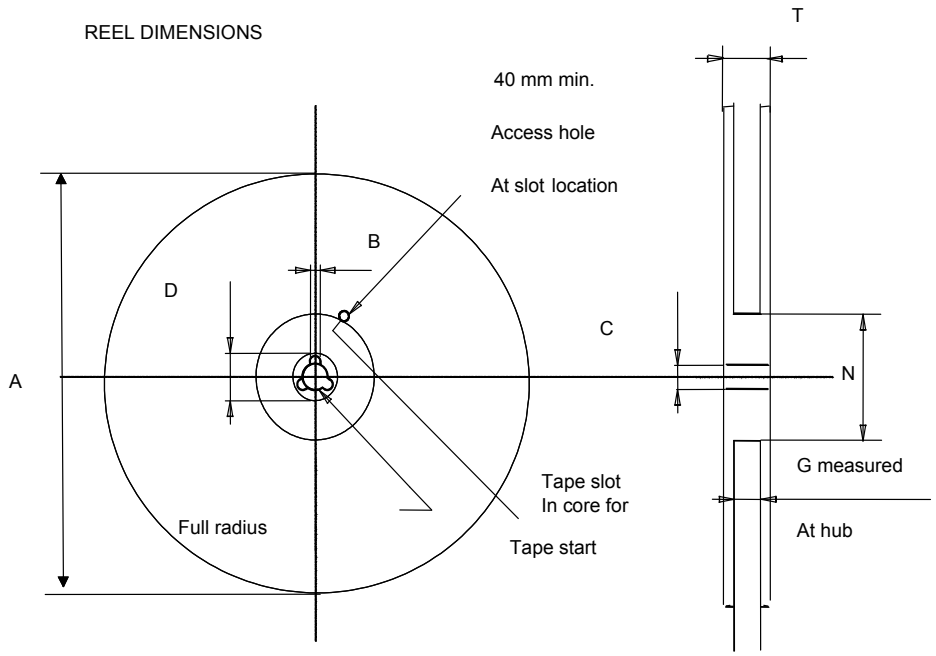


Table 8. Tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.30	0.40			
W	23.7	24.3			

Revision history

Table 9. **Document revision history**

Date	Revision	Changes
16-Aug-2024	1	First release.
17-Jan-2025	2	Updated Table 3. Static characteristics.

Contents

1 **Electrical ratings** 2
2 **Electrical characteristics** 3
2.1 Electrical characteristics (curves) 5
3 **Test circuits** 9
4 **Package information** 10
4.1 H²PAK-7 package information 10
4.2 Packing information 12
Revision history 14

IMPORTANT NOTICE – READ CAREFULLY

STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST’s terms and conditions of sale in place at the time of order acknowledgment.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of purchasers’ products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. For additional information about ST trademarks, refer to www.st.com/trademarks. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.